



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re U.S. Patent Application of:

INVENTORS: Kim et al.

SERIAL NO.: 10/733,537

ART UNIT: 2819

FILED: 12/11/2003

EXAMINER: Unknown

TITLE: Performance Increase Technique For Use In A Register File

Having Dynamically Boosted Wordlines

ATTORNEY DOCKET NO.: YOR920030543US1

Commissioner For Trademarks

P.O. Box 1450

Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Dear Sir:

Pursuant to Sections 609 and 707.05(b) of the MPEP and 37 CFR 1.97-1.99, the attached form PTO-1449 lists documents, which may be pertinent to the invention as claimed in the above-identified application. Copies are herewith submitted of the non-U.S. documents and publications.

The citation of these documents should not be construed as a representation that a thorough search has been made, or that other, more pertinent material is not available.

Respectfully submitted,

Harry F. Smith (Reg. No. 32,493)

HARRINGTON & SMITH, LLP

4 Research Drive

Shelton, CT 06484-6212

(203)925-9400

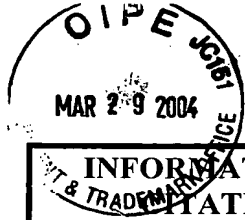
Customer No.: 29683

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail on the date shown below in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

3/24/2004
Date

Clarence F. Mason
Name of Person Making Deposit



INFORMATION DISCLOSURE CITATION FORM FOR PATENT APPLICATION (FORM PTO-1449) (Substitute)	Docket No.: 909A.0150.U1(US)	Serial No.: 10/733,537
	Applicant(s): Kim et al.	
	Filing Date: 12/11/03	Group: 2819

U.S. PATENT DOCUMENTS

Examiner Initials	Document Number (Number-Kind Code)	Publication Date (MM-DD-YYYY)	Name of Patentee or Applicant	Class	Sub-class
	US- US- US- US- US- US- US- US- US- US- US- US- US- US- US-				

FOREIGN PATENT DOCUMENTS

Examiner Initials	Document Number (Country Code-Number-Kind Code)	Publication Date (MM-DD-YYYY)	Name Of Patentee of Applicant	Translation? Yes/No/n/a
	- - - - - - - - - - - -			

OTHER DOCUMENTS (Author (Capitalize), Title, Date, Pages, Etc., if known)

	"A Precise On-Chip Voltage Generator for a Gigascale DRAM with a Negative Word-Line Scheme", Hitoshi Tanaka et al., IEEE Jurnal of Solid-State Circuits, Vol. 34, No. 8, August 1999, pp. 1084-1090
	"A 130-nm 6-GHz 256 x 32 bit Leakage-Tolerant Register File, Ram K. Krishnamurthy, et al., IEEE Journal of Solid-State Circuits, Vol. 37, No. 5, May 2002, pp. 624-632
	"Session 10/Low-Power & Communication Signal Processing/Paper FA10.3", Tadahiro Kuroda et al.,
	"Dynamic Fine-Grain Leakage Reduction Using Leakage-Biased Bitlines", Seongmoo Heo et al., IEEE Proceedings of the 29 th Annual International symposium on Computer Architecture, 2002, 11 pages
	"Dynamic Leakage Cut-off Scheme for Low-Voltage SRAM's", Hiroshi Kawaguchi, et al., IEEE Symposium on VLSI Circuits Digest of Technical Papers, 1998, pp. 140-141

Examiner's Signature:

Date Considered:

Initial if reference was considered, whether or not citation is in conformance with MPEP. Mark through citation if not considered.
Include a copy of this citation form with your next correspondence to the Applicant(s).